NST847BF3T5G

NPN General Purpose Transistor

The NST847BF3T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563/SOT-963 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-1123 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

Features

- h_{FE}, 200–450
- Low $V_{CE(sat)}$, $\leq 0.25 \text{ V}$
- Reduces Board Space
- This is a Pb–Free Device

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	45	Vdc
Collector – Base Voltage	V _{CBO}	50	Vdc
Emitter – Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ι _C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, T _A = 25°C Derate above 25°C	P _D (Note 1)	290 2.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 1)	432	°C/W
Total Device Dissipation, T _A = 25°C Derate above 25°C	P _D (Note 2)	347 2.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 2)	360	°C/W
Thermal Resistance, Junction-to-Lead 3	R _{ΨJL} (Note 2)	143	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	−55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

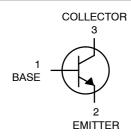
1. 100 mm² 1 oz, copper traces.

2. 500 mm² 1 oz, copper traces.



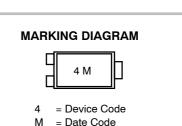
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http://onsemi.com



NST847BF3T5G





ORDERING INFORMATION

Device	Package	Shipping [†]
NST847BF3T5G	SOT-1123 (Pb-Free)	8000/Tape & Reel

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NST847BF3T5G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

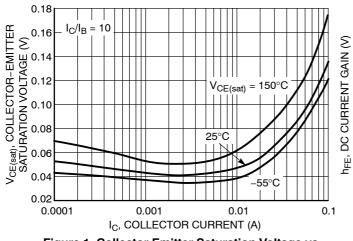
Cł	naracteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Vol	tage (I _C = 10 mA)	V _{(BR)CEO}	45	-	-	V
Collector – Emitter Breakdown Vol	tage (I _C = 10 μA, V _{EB} = 0)	V _{(BR)CES}	50	-	-	V
Collector - Base Breakdown Volta	ge (I _C = 10 μA)	V _{(BR)CBO}	50	-	_	V
Emitter – Base Breakdown Voltage	e (I _E = 1.0 μA)	V _{(BR)EBO}	6.0	-	_	V
Collector Cutoff Current	(V _{CB} = 30 V) (V _{CB} = 30 V, T _A = 150°C)	I _{CBO}	-	-	15 5.0	nA μA

ON CHARACTERISTICS

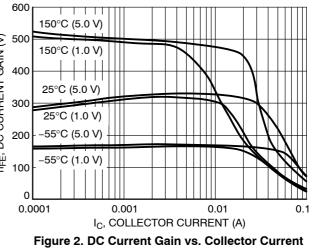
	h _{FE}	_ 200	150 290	_ 450	-
Collector – Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA)	V _{CE(sat)}	-	-	0.25 0.6	V
Base – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)	V _{BE(sat)}	-	0.7 0.9	-	V
Base – Emitter Voltage (I _C = 2.0 mA, V _{CE} = 5.0 V) (I _C = 10 mA, V _{CE} = 5.0 V)	V _{BE(on)}	580 -	660 -	700 770	mV

SMALL-SIGNAL CHARACTERISTICS

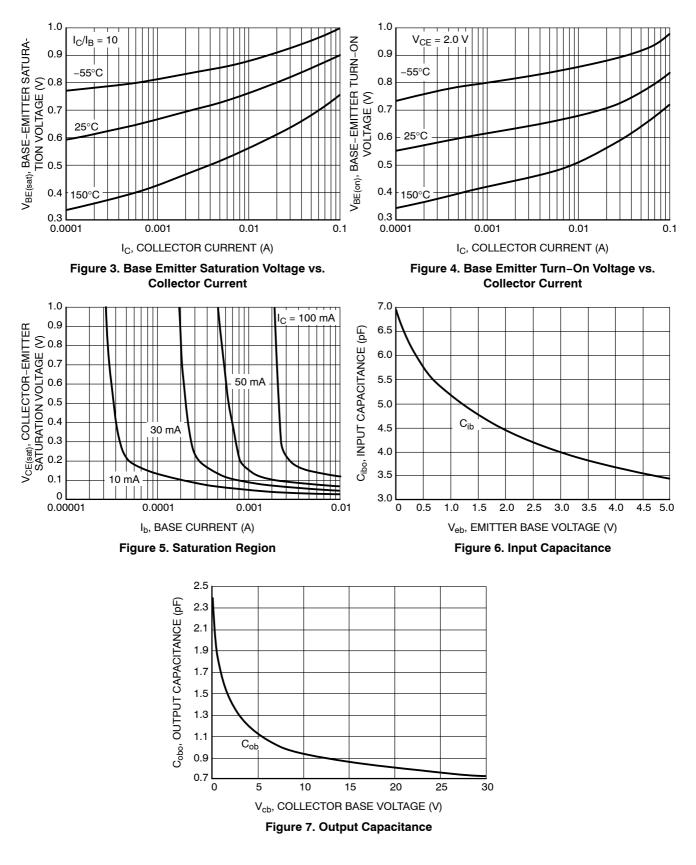
Current – Gain – Bandwidth Product $(I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ Vdc}, f = 100 \text{ MHz})$	f _T	100	-	_	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}	-	-	4.5	pF
Input Capacitance (V_{EB} = 0.5 V, I_C = 0 mA, f = 1.0 MHz)	C _{ibo}	-	-	10	pF
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 Vdc, R _S = 2.0 k Ω , f = 1.0 kHz, BW = 200 Hz)	NF	-	-	10	dB







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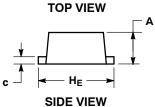




SCALE 8:1



SOT-1123 CASE 524AA ISSUE C





SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE	2. SOURCE
3. COLLECTOR	3. CATHODE	3. CATHODE	3. ANODE	3. DRAIN

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DESCRIPTION:	SOT-1123, 3-LEAD, 1.0X0	.6X0.37, 0.35P	PAGE 1 OF 1
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DATE 29 NOV 2011

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE
- MINIMUM THICKNESS OF BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.34	0.40	
b	0.15	0.28	
b1	0.10	0.20	
С	0.07	0.17	
D	0.75	0.85	
Е	0.55	0.65	
е	0.35	0.40	
HE	0.95	1.05	
L	0.185 REF		
L2	0.05	0.15	

GENERIC MARKING DIAGRAM*

X = Specific Device Code M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " •", may or may not be present.

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